

# Caroline B Lim

## List of Publications by Year in descending order

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12  
papers

205  
citations

1040056

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1199594

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g-index

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all docs

13  
docs citations

13  
times ranked

287  
citing authors

#	ARTICLE	IF	CITATIONS
1	Ge doping of GaN beyond the Mott transition. <i>Journal Physics D: Applied Physics</i> , 2016, 49, 445301.	2.8	36
2	Nonpolar $m$ -plane GaN/AlGaN heterostructures with intersubband transitions in the 5–10 THz band. <i>Nanotechnology</i> , 2015, 26, 435201.	2.6	26
3	Intersubband transitions in nonpolar GaN/Al(Ga)N heterostructures in the short- and mid-wavelength infrared regions. <i>Journal of Applied Physics</i> , 2015, 118, 014309.	2.5	26
4	Effect of doping on the intersubband absorption in Si- and Ge-doped GaN/AlN heterostructures. <i>Nanotechnology</i> , 2017, 28, 405204.	2.6	24
5	Long-lived excitons in GaN/AlN nanowire heterostructures. <i>Physical Review B</i> , 2015, 91, .	3.2	17
6	Effect of doping on the far-infrared intersubband transitions in nonpolar $m$ -plane GaN/AlGaN heterostructures. <i>Nanotechnology</i> , 2016, 27, 145201.	2.6	16
7	Intersubband absorption in Si- and Ge-doped GaN/AlN heterostructures in self-assembled nanowire and 2D layers. <i>Physica Status Solidi (B): Basic Research</i> , 2017, 254, 1600734.	1.5	16
8	Short-wave infrared ( $\lambda = 3\mu\text{m}$ ) intersubband polaritons in the GaN/AlN system. <i>Applied Physics Letters</i> , 2017, 110, .	3.3	12
9	Gallium kinetics on $m$ -plane GaN. <i>Applied Physics Letters</i> , 2017, 111, .	3.3	11
10	Short-wavelength, mid- and far-infrared intersubband absorption in nonpolar GaN/Al(Ga)N heterostructures. <i>Japanese Journal of Applied Physics</i> , 2016, 55, 05FG05.	1.5	9
11	Effect of Al incorporation in nonpolar $m$ -plane GaN/AlGaN multi-quantum-wells using plasma-assisted molecular-beam epitaxy. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2017, 214, 1600849.	1.8	6
12	Effect of Ge-doping on the short-wave, mid- and far-infrared intersubband transitions in GaN/AlGaN heterostructures. <i>Semiconductor Science and Technology</i> , 2017, 32, 125002.	2.0	6